The SENSEI Experiment: Origin and characterization of single-electron events

> Mariano Cababie TU Wien / HEPHY

for the SENSEI* Collaboration 2023 EXCESS@TAUP

*Sub-Electron-Noise Skipper-CCD Experimental Instrument

The SENSEI Collaboration

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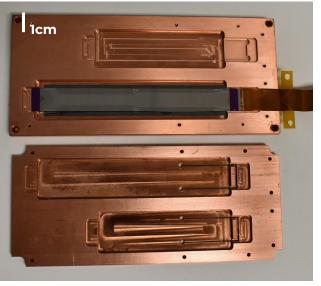






The SENSEI Experiment

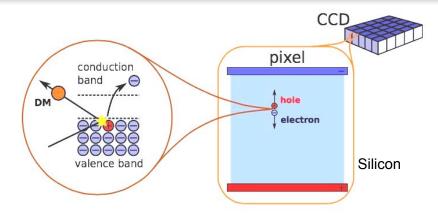


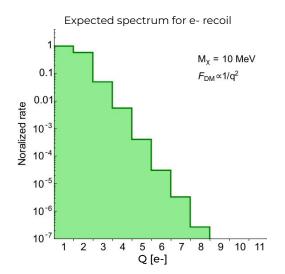


- ⇒ Si Skipper Charge-Coupled Devices (SENSEI, DAMIC, DAMIC-M, OSCURA)
- ⇒ Probes sub-GeV DM via e- recoil and (~eV) DM absorption
- ⇒ Sub-electronic (~0.1 e-) readout noise
- ⇒ Energy threshold as low as ~1.1 eV (Silicon bandgap)
- ⇒ Lowest single-electron rate (~le-4 e-/pix/day) in Silicon semiconductors.
- ⇒ Developed by **LBNL** MicroSystems Lab Energy

Electron recoils for sub-GeV DM in Skipper-CCDs

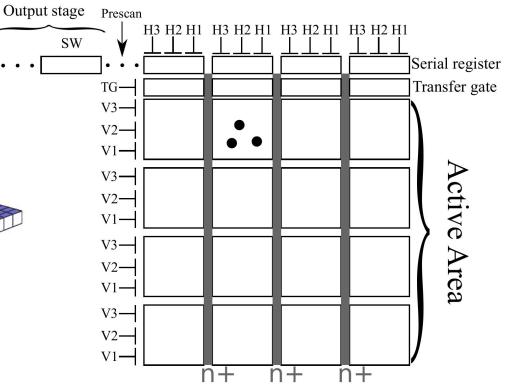
- DM candidates:
 - Sub-Gev DM-e⁻ scattering
 - Dark photon absorption
 - mCP (**new!** arXiv:2305.04964)
- * Silicon SCCDs as ionization detectors
 - Energy transfer via electron recoil (or absorption)
 - Ionized h^+ are captured and stored by SCCD.
 - Signal is readout afterwards.

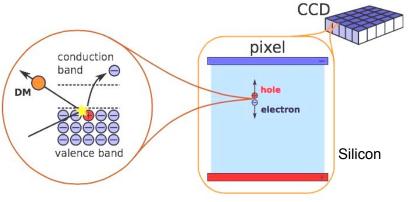




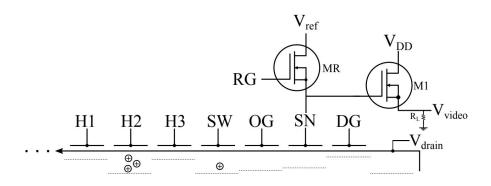
CCD basics

- CCD = pixelated silicon array
- Collect, store and read
- **~2/2.5g** per device
- * ~5.5Mpixels of $15x15x675 \mu m^3$ each



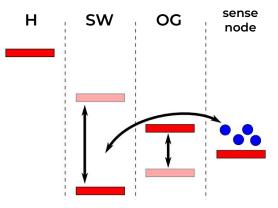


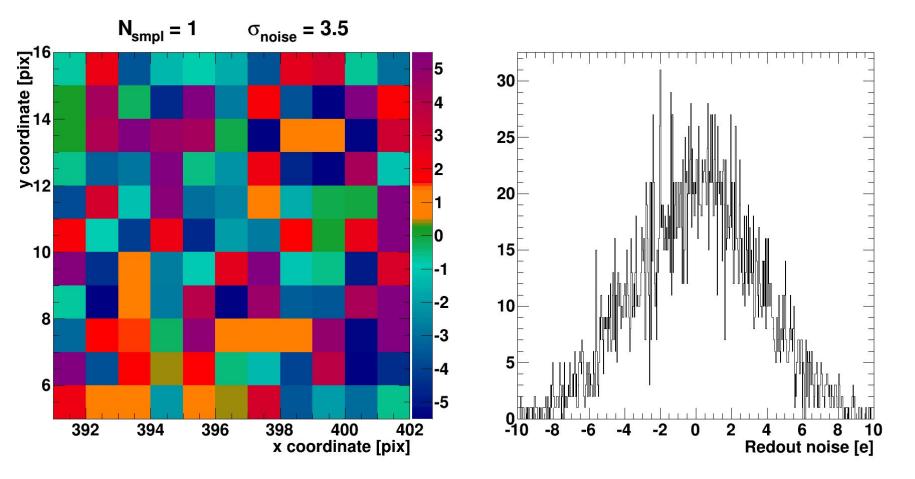
- In a conventional CCD, charge is moved to the sense node and readout once.
 Then it is drained and charge is lost.
- Longer integration reduces noise but cannot reduce **1/f** noise.
- Skipper-CCD moves charges towards and backwards the floating sense node to achieve multiple non-destructive readout

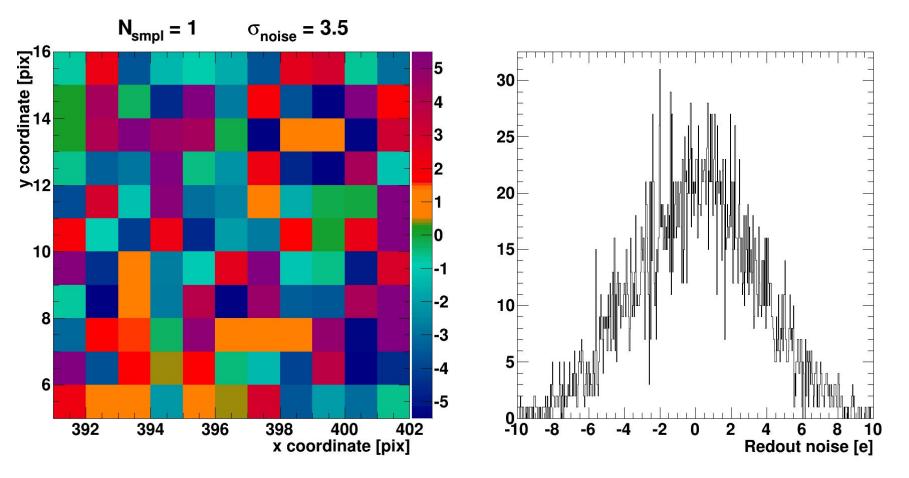


Skipper-CCD output stage

The Skipper technology

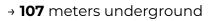






Locations: where is SENSEI?

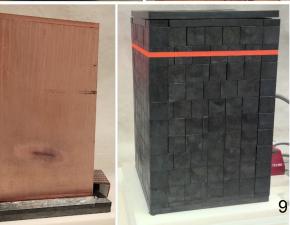




- → 1 device (2 grams) installed
- → Same site as dev site

- Final location +
- 2 kilometers underground +
 - 6 devices (15g) installed * +
 - Near dev site (Canada) ←





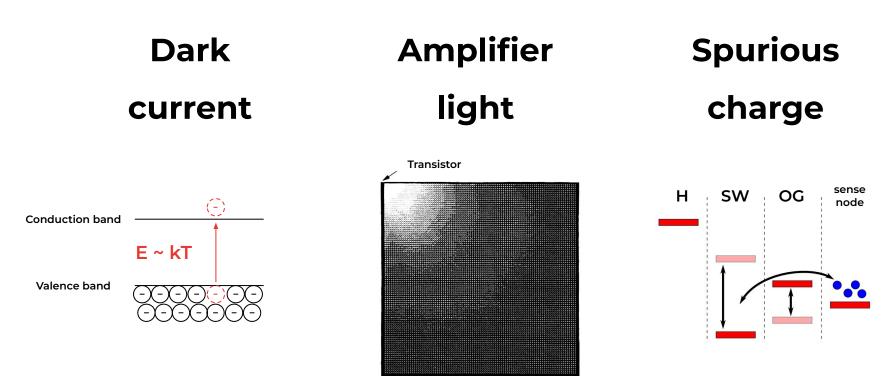
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CCD

MINOS H

NuMI building

Single Electron Event (SEE) contributions



Single Electron Event (SEE) contributions

Dark	Amplifier	Spurious	
current	light	charge	

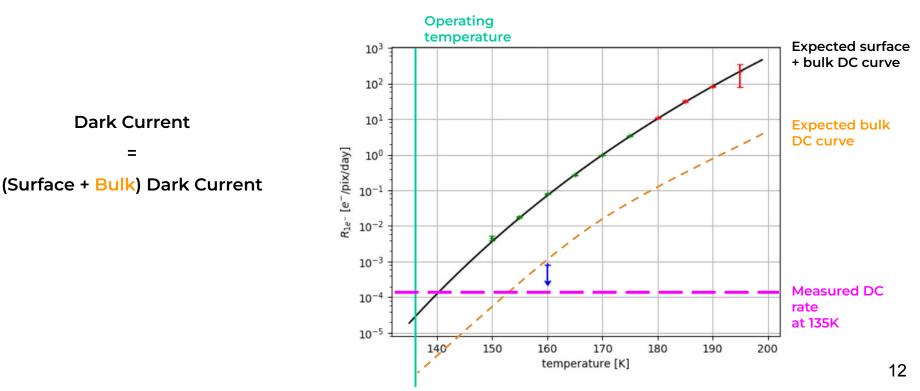
$$\mu_{(t_{EXP},t_{RO})} = \lambda_{DC} \, t_{EXP} + (rac{\lambda_{DC}}{2} + \lambda_{AL}) \, t_{RO} + \mu_{SC}$$

11

Dark current

→ Dark current rate (presumably from thermal agitation) is higher than the expected (theoretical) at 135K

$$1.6 imes 10^{-4}e-/pix/day>>\sim 1 imes 10^{-6}e-/pix/day$$

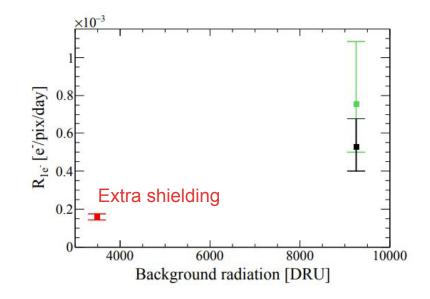


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 \rightarrow Origin? Du, Egana, Essig and Sholapurkar (2011.13939) proposed the source of this discrepancy may come from the interaction of high energy events with the CCD as it is was hinted in SENSEI2020@MINOS:

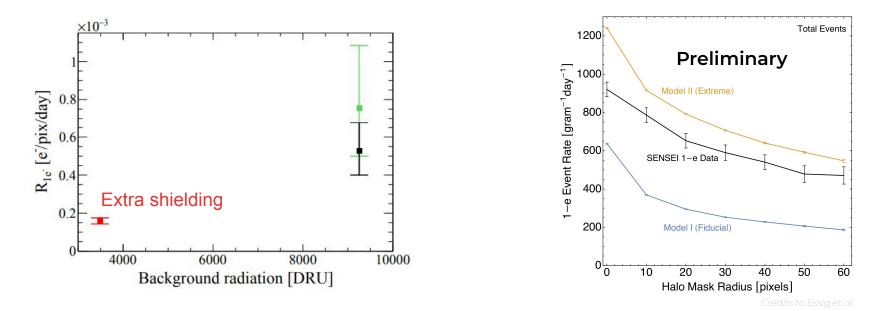


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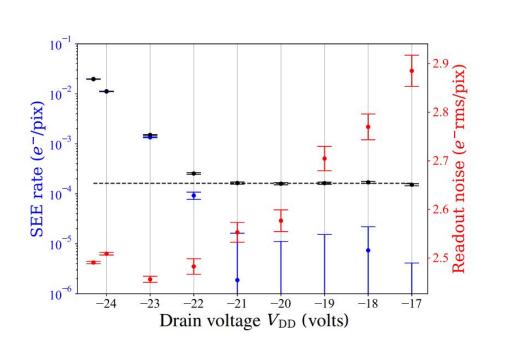
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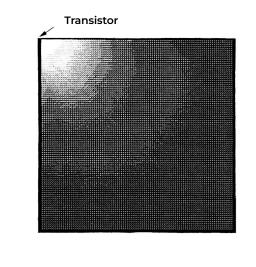
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Amplifier light study

→ How does output transistor bias voltage affect light emission and readout noise?

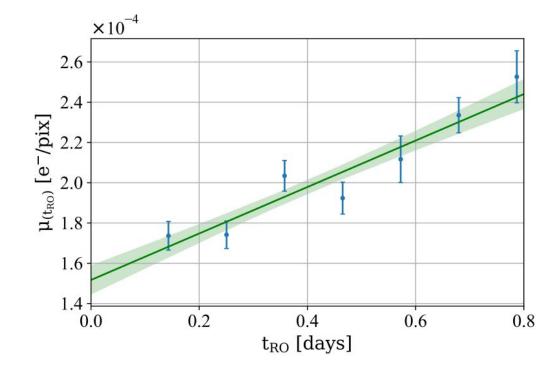




V_{DD}	$\lambda_{\rm AL}~(10^{-4}~e^-/{\rm pix/day})$
-21	(0.36 ± 0.18)
-22	(19.91 ± 1.26)

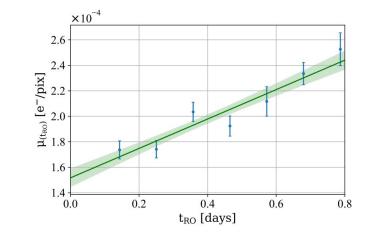
Determination of contributions

$$\mu_{(t_{EXP},t_{RO})} = \lambda_{DC} \, t_{EXP} + (rac{\lambda_{DC}}{2} + \lambda_{AL}) \, t_{RO} + \mu_{SC}$$



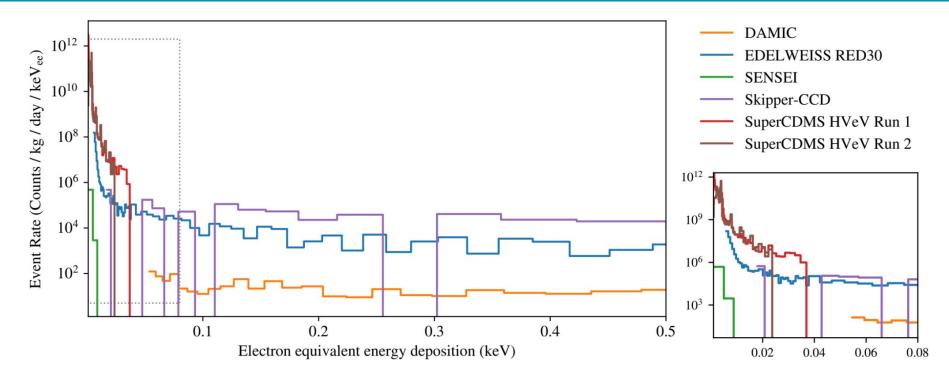
Determination of contributions

$$\mu_{(t_{EXP},t_{RO})} = \lambda_{DC} \, t_{EXP} + (rac{\lambda_{DC}}{2} + \lambda_{AL}) \, t_{RO} + \mu_{SC}$$



\mathbf{V}_{DD}	External Shield	$\lambda_{ m DC}$	$\lambda_{ m AL}$	$\mu_{ m SC}$
-21	Yes	(1.59 ± 0.16)	(0.36 ± 0.18)	(1.52 ± 0.07)
		$10^{-4} e^-/\mathrm{pix/day}$	$10^{-4} e^-/\text{pix/day}$	$10^{-4} e^{-}/{\rm pix}$

Last report @ EXCESS Feb 2022

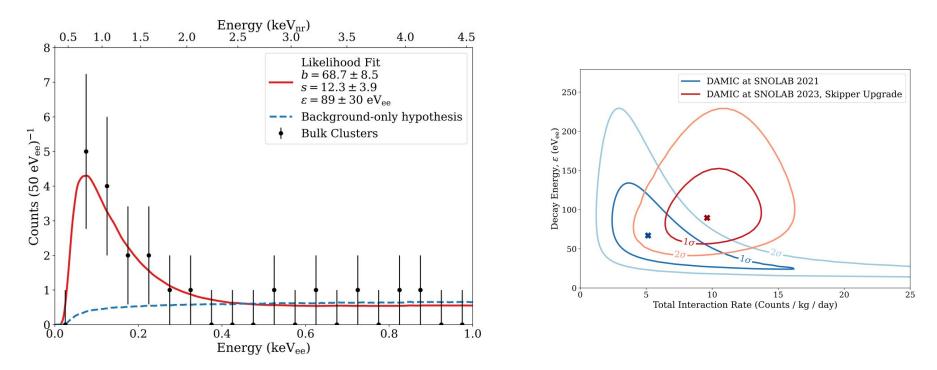


→ This is the result presented for 2020@MINOS run, new update coming soon for SNOLAB first run.

→ No excess reported but take in mind single-electron event resolution + particle discrimination.

 \rightarrow Spatial correlation of high energy events (>O(100keV)) with 1e- events: cherenkov radiation / radiative recombination (arXiv:2011.13939). Talk with Daniel!

SCCD EXCESS @ SNOLAB



→ No exponential rise with lower-energies: rejection of surface events discards first-bin events.

- → Not explained (yet) by any background model.
- → SENSEI@SNOLAB (and DAMIC-M@LSM) will probe this excess very soon.

Second science run @ SNOLAB

Latest results from the SENSEI experiment on sub-GeV dark matter searches

31 ago 2023, 14:45
15m
Hörsaal 3 lecture hall (University of Vienna)



Detailed results

mCP exclusion limits

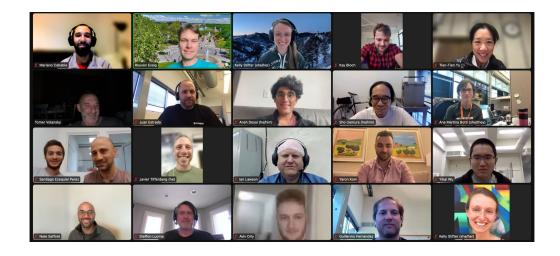
Ponente

💄 Ana Martina Botti (Fermilab)

✤ Last SNOLAB visit

The SENSEI Collaboration





Thank you! Any questions?

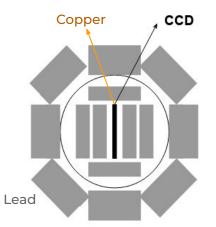
The SENSEI Collaboration



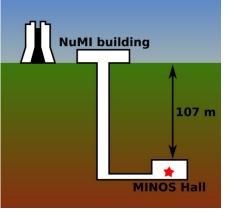
⁄ensei

MINOS2020 setup: location and shielding

- Underground site reduces muon environmental radiation
- Inner (1" each) and outer (2" each) lead bricks
 reduces gamma environmental radiation
- Copper module for **IR** radiation
- Temperature at **135K** and high-vacuum regime.
- Operated with specifically designed readout electronics
 - (LTA Low Threshold Acquisition board)

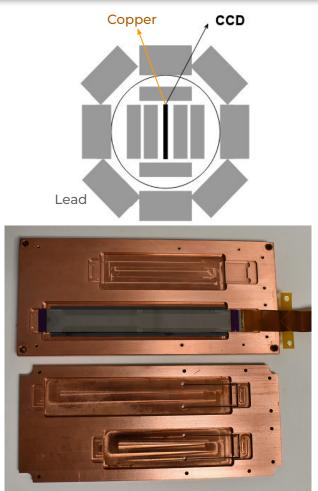






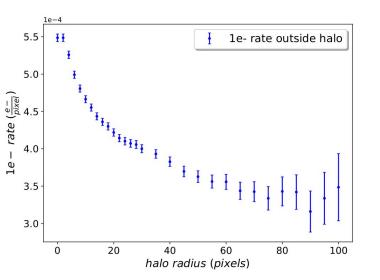
MINOS shielding





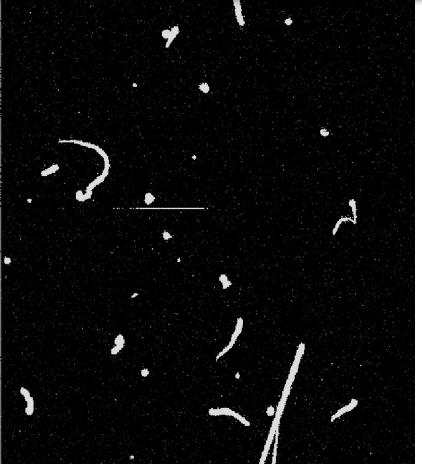


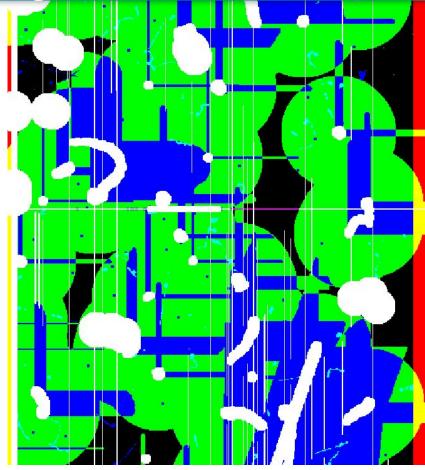
Single electron event rate



 Spatial correlation between high energy events (>360eV) and 1e- events.

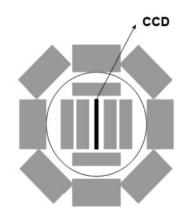
Sample image

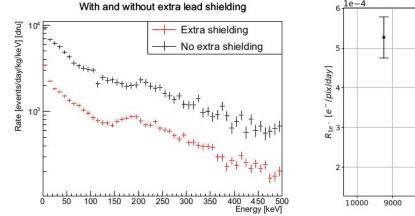


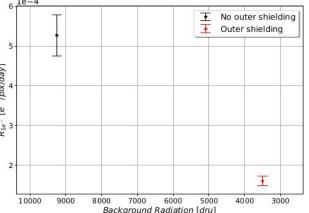


1e- rate vs. shielding

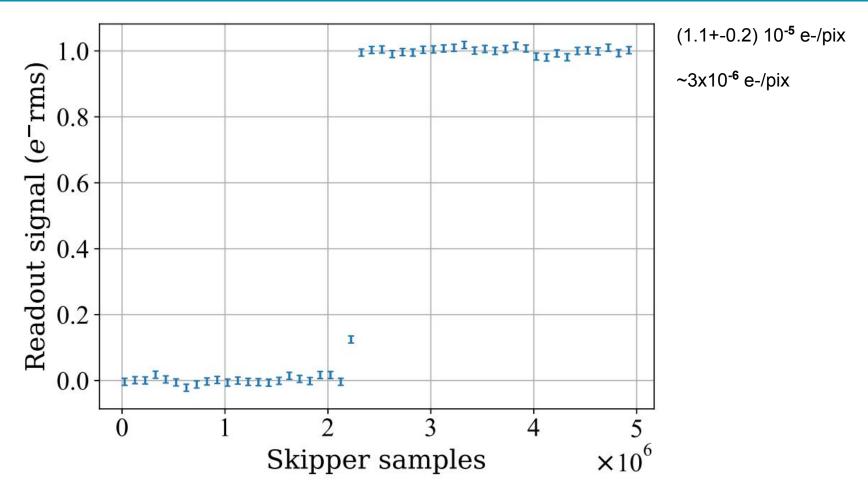
- We have data with and without the outer ring of lead bricks
- Factor of 3 reduction in the rate of high-energy tracks → factor of 3 reduction in the 1e⁻ rate
 - There is some mechanism by which ionizing radiation generates charge uniformly in our CCD
 - Better shielding will very likely further reduce our 1e⁻ rate



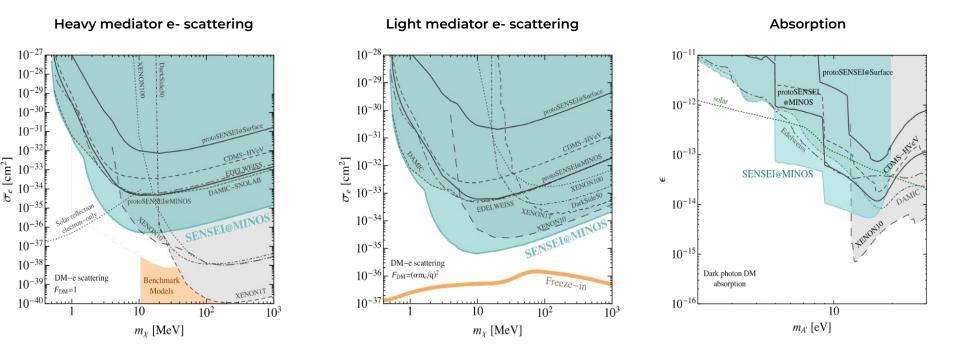




SC@Sense node



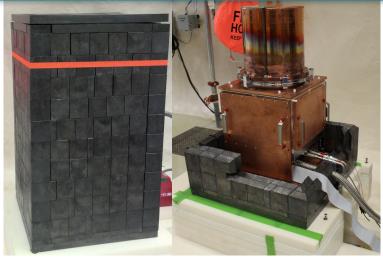
Latest Results: SENSEI@MINOS



SENSEI@SNOLAB

- **Extraordinary** support from SNOLAB during COVID-19 pandemic
 - 6 CCDs (**15g**) deployed.
 - 2km of granite, 3" of lead, 20" of polyethylene and water

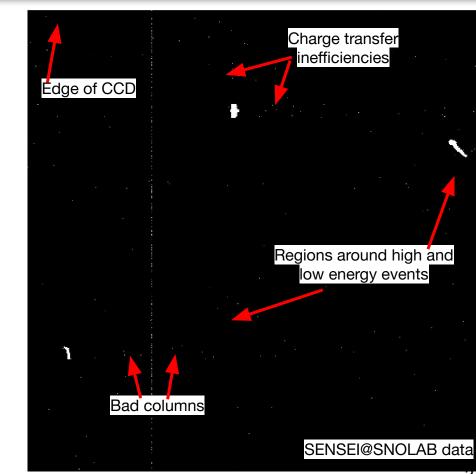




- First science run of SENSEI@SNOLAB
 - 6 months of data-taking: 129 images, no binning, 50% blinded
 - \circ 300 Skipper samples \rightarrow 0.14e- noise
 - 1 e- density (after cuts): ~2 x 10⁻⁴ e-/pixel

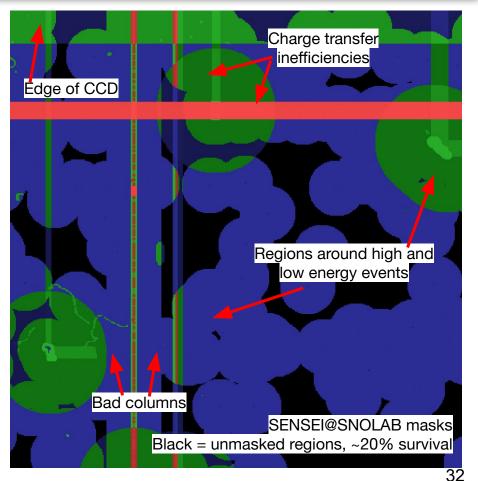
SENSEI@SNOLAB: event selection criteria

- Electronic noise
- Crosstalk
- Edges of CCDs
- Bad pixels/columns
- Serial register hits
- Bleeding (CTI)
- High-energy halo
- Low-energy halo

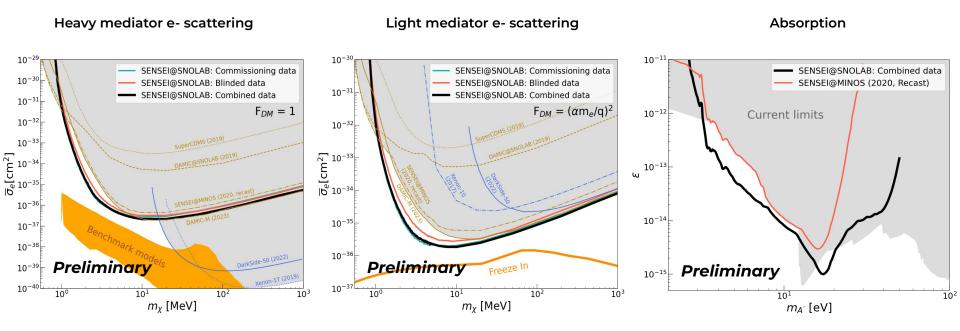


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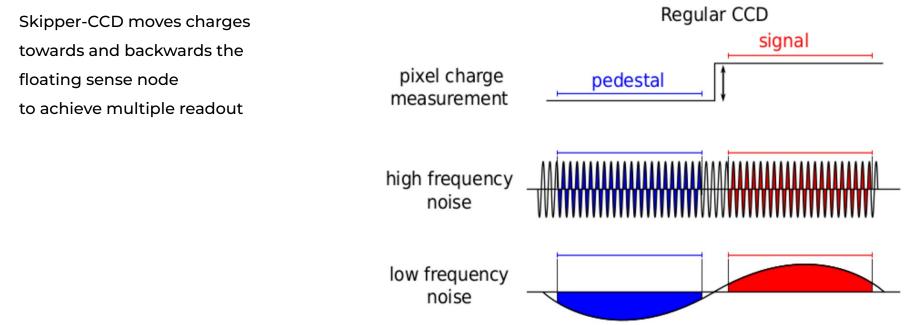
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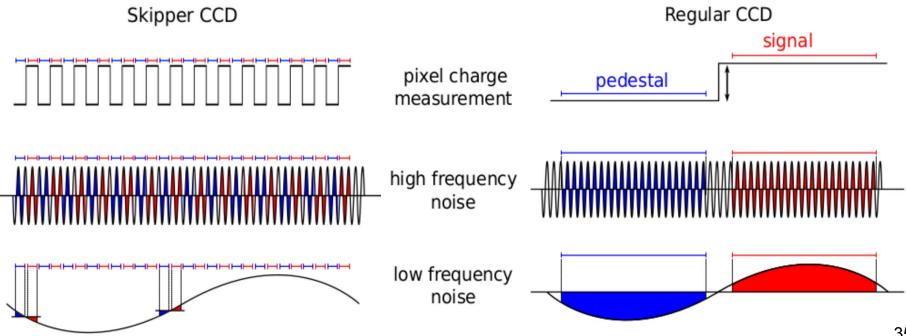
SENSEI@SNOLAB: results



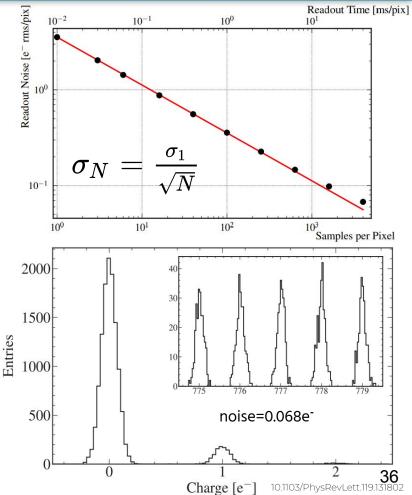
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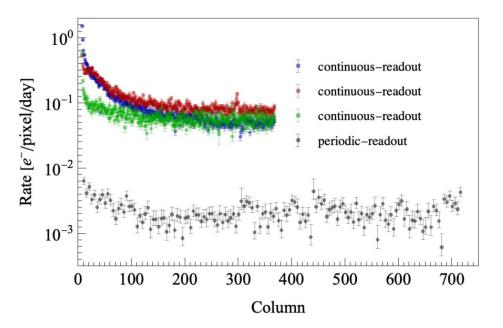


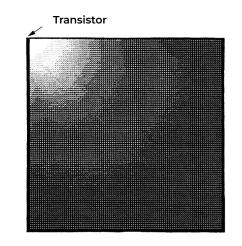
- Skipper technology allows to read repeatedly the same pixel to achieve sub-electron noise
- ~ 2e- noise goes to<0.1e⁻ using the skipper technology
- Low energy threshold down to ~1.1eV (Si band gap)
- Capability of unambiguously count clusters of few electrons
- 15x15 μm² pixels allow for spatial resolution of events



Amplifier light

- → Increases linearly with time but spatially localized near the readout stage.
- \rightarrow In SENSEI 2019 this effect was a mayor SEE contributor





Amplifier light study

→ How does output transistor bias voltage affect light emission and readout noise?

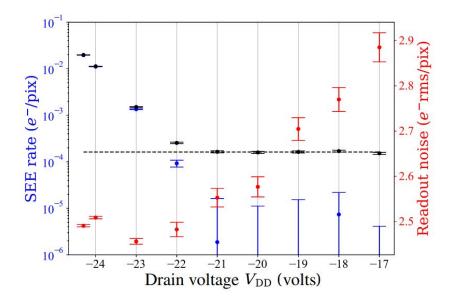


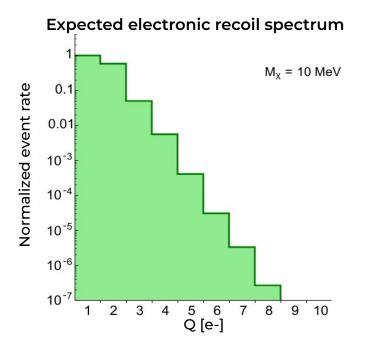
FIG. 5. SEEs per pixel (left axis) and single-sample readout noise (red, right axis) as a function of the drain voltage of the M1 transistor (V_{DD}). In black, we show the SEEs per pixel collected for each voltage ($\mu_{(t_{ro})}$) and in blue the AL contribution (μ_{AL}), estimated from Eq. (6). The black dashed line shows the estimation for μ_{SC} . Images are taken from dataset *B*.

V_{DD}	$\lambda_{\rm AL}~(10^{-4}~e^-/{\rm pix/day})$
-21	(0.36 ± 0.18)
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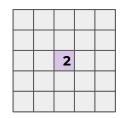
Why are SEEs relevant?

⇒ Because of spatial random coincidence of SEEs can generate higher

energy events

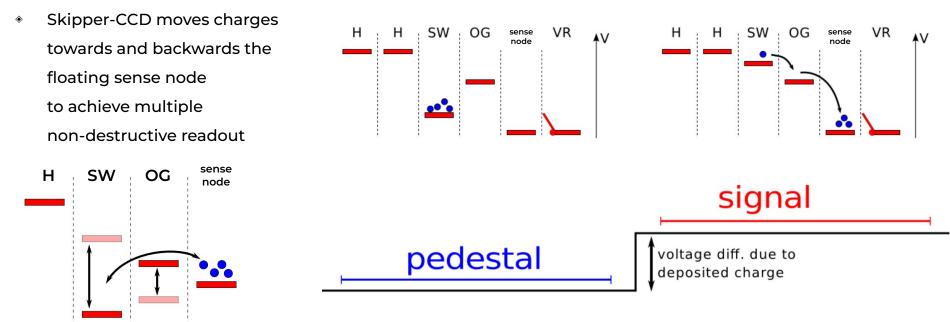


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	1		

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Single Electron Event (SEE) contributions

$\begin{array}{c} \textbf{Contribution} \\ \textbf{(}e^{-}/\text{pix}\textbf{)} \end{array}$		Time dependence			Smotial
		Linear		Independent	Spatial distribution
		Exposure	Readout	independent	distribution
Dark	Intrinsic	$\lambda_{ m DC} \; t_{ m EXP}$	$rac{\lambda_{ m DC}}{2} t_{ m RO}$	-	Uniform
current	Extrinsic				Uniform
Amplifie	er-light current	-	$\lambda_{ m AL} \; t_{ m RO}$	-	Localized
Spur	ious charge	-	-	$\mu_{ m SC}$	Uniform

$\mathbf{V}_{\mathbf{D}\mathbf{D}}$	External Shield	$\lambda_{ m DC}$	$\lambda_{ m AL}$	$\mu_{ m SC}$
-21	Yes	(1.59 ± 0.16)	(0.36 ± 0.18)	(1.52 ± 0.07)
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